# ELECTRONIC DEVICES ASSIGNMENT 1

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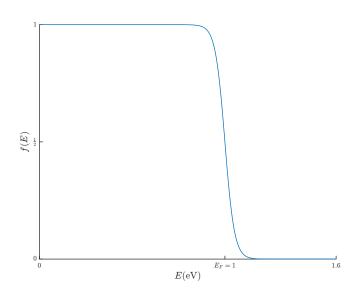
# Exercise 1.

- (1) Plot the Fermi function at room temperature for  $E_f=1\,\mathrm{eV}$ . Plot over the energy range  $0\,\mathrm{eV}-1.6\,\mathrm{eV}$ . Calculate data points every  $0.2\,\mathrm{eV}$ . Attach a table of calculated values along with your plot.
- (2) Show that the probability of an occupied state  $\Delta E$  above  $E_f$  is equal to the probability of an empty state  $\Delta E$  below  $E_F$ , i.e.

$$f(E_F + \Delta E) = 1 - f(E_F - \Delta E)$$

## Solution 1.

(1)



Date: Thursday 10<sup>th</sup> March, 2016.

E(eV)	f(E)
0	1
0.2	0.99999999999964
0.4	0.99999999916739
0.6	0.999999809324428
0.8	0.99956352640943
1	0.5
1.2	0.000436473590570019
1.4	$1.90675572317553 \times 10^{-7}$
1.6	$8.32612088642445 \times 10^{-11}$

(2)

$$f(E) = \frac{1}{1 + e^{\frac{E - E_F}{kT}}}$$

$$\therefore f(E_F + \Delta E) = \frac{1}{1 + e^{\frac{E_F + \Delta E - E_F}{kT}}}$$

$$= \frac{1}{1 + e^{\frac{\Delta E}{kT}}}$$

$$\therefore f(E_F - \Delta E) = \frac{1}{1 + e^{\frac{E_F - \Delta E - E_F}{kT}}}$$

$$= \frac{1}{1 + e^{-\frac{\Delta E}{kT}}}$$

$$= \frac{e^{\frac{\Delta E}{kT}}}{e^{\frac{\Delta E}{kT}} + 1}$$

$$= 1 - \frac{1}{e^{\frac{\Delta E}{kT}} + 1}$$

$$= 1 - f(E_F + \Delta E)$$

## Exercise 2.

A N-type semiconductor has the following properties.

- $\begin{aligned} &(1) \ E_{\rm gap} = 1.1\,{\rm eV}.\\ &(2) \ N_C = N_V.\\ &(3) \ N_D = 10^{15}{\rm cm}^{-3}. \end{aligned}$
- (4)  $E_D = E_C 0.2 \,\text{eV}$ .

Given that  $E_f$  is  $0.25\,\mathrm{eV}$  below  $E_C$ , calculate  $n_i$ , and the concentration of the electrons and holes in the semiconductor at 300 K.

#### Solution 2.

$$n = n_i e^{\frac{E_F - E_i}{kT}}$$

$$\therefore N_D = n_i e^{\frac{E_F - E_i}{kT}}$$

$$\therefore 10^{15} = n_i e^{\frac{0.3}{2585.1 \times 10^{-5}}}$$

$$\therefore 10^{15} = n_i e^{11.605}$$

$$\therefore n_i = \frac{10^{15}}{e^{11.605}}$$

$$= 9.12 \times 10^9$$

Therefore,

$$p = \frac{n_i^2}{n}$$

$$= \frac{83.1744 \times 10^{18}}{10^{15}}$$

$$= 83.1744 \times 10^3$$

## Exercise 3.

A semiconductor has an intrinsic carrier concentration of  $10^{10}$  cm<sup>-3</sup> at 300 K, and its conduction and valence band effective densities of states are equal to  $10^{19}$  cm<sup>-3</sup>, i.e.,  $N_C = N_V = 10^{19}$  cm<sup>-3</sup>.

- (1) What is the band gap  $E_{\rm gap}$ ?
- (2) If the semiconductor is doped with  $N_D = 10^{16} \text{cm}^{-3}$ , what are the equilibrium electron and hole concentrations at 300 K?
- (3) If the same piece of semiconductor, already having  $N_D = 10^{16} \text{cm}^{-3}$ , is now also doped with acceptors with  $N_A = 2 \times 10^{16} \text{cm}^{-3}$ , what are the new equilibrium electron and hole concentrations at 300 K? What is the Fermi level position with respect to the intrinsic Fermi level, i.e., what is  $E_f E_i$ ?

# Solution 3.

$$n_{i} = \sqrt{N_{C}N_{V}}e^{-\frac{E_{\text{gap}}}{2kT}}$$

$$\therefore \frac{n_{i}}{\sqrt{N_{C}N_{V}}} = e^{-\frac{E_{\text{gap}}}{2kT}}$$

$$\therefore E_{\text{gap}} = -2kT \ln\left(\frac{n_{i}}{\sqrt{N_{C}N_{V}}}\right)$$

$$= -(2)(8.617)(300) \ln\left(\frac{10^{10}}{10^{19}}\right)$$

$$= -\left(5170.2 \times 10^{-5}\right) \ln\left(10^{-9}\right)$$

$$= -\left(5170.2 \times 10^{-5}\right) (-20.723)$$

$$= 107142.0546 \times 10^{-5}$$

$$= 1.071420546 \text{ eV}$$

# (2)

$$n = N_D$$

$$= 10^{16} \text{cm}^{-3}$$

$$p = \frac{n_i^2}{n}$$

$$= \frac{10^{20}}{10^{16}}$$

$$= 10^4 \text{cm}^{-3}$$

# (3)

$$p = N_A - N_D$$

$$= 10^{16} \text{cm}^{-3}$$

$$n = \frac{n_i^2}{p}$$

$$= \frac{10^{20}}{10^{16}}$$

$$= 10^4 \text{cm}^{-3}$$

Therefore,

$$n = n_i e^{\frac{E_F - E_i}{kT}}$$

$$\therefore 10^4 = 10^{10} e^{\frac{E_F - E_i}{(8.617 \times 10^{-5})(300)}}$$

$$\therefore 10^{-6} = e^{\frac{E_F - E_i}{2585.1 \times 10^{-5}}}$$

$$\therefore \ln \left(10^{-6}\right) = \frac{E_F - E_i}{2585.1 \times 10^{-5}}$$

$$\therefore E_F - E_i = (-13.8155) \left(2585.1 \times 10^{-5}\right)$$

$$= -0.3571444905$$